

Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Complementary PNP Type Available (DSS9110Y)
- Ultra Small Surface Mount Package
- **"Lead Free", RoHS Compliant (Note 1)**
- **Halogen and Antimony Free, "Green Device" (Note 2)**

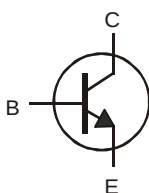
Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)

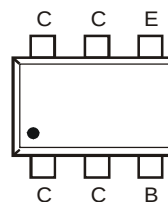
SOT-363



Top View



Device Symbol



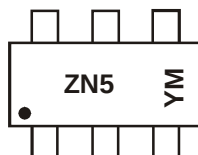
Pin-Out Top

Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS8110Y-7	ZN5	7	8mm	3,000

- Notes:
1. No purposefully added lead.
 2. Diode's Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



ZN5 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: X = 2010)
 M = Month (ex: 9 = September)

Date Code Key

Year	2010	2011	2012	2013	2014	2015
Code	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	1	A
Peak Pulse Collector Current	I_{CM}	3	A
Base Current - Continuous	I_B	0.3	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ $T_A = 25^\circ\text{C}$	P_D	625	mW
Thermal Resistance, Junction to Ambient (Note 4) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 4. Device mounted on FR-4 PCB, with minimum recommended pad layout.

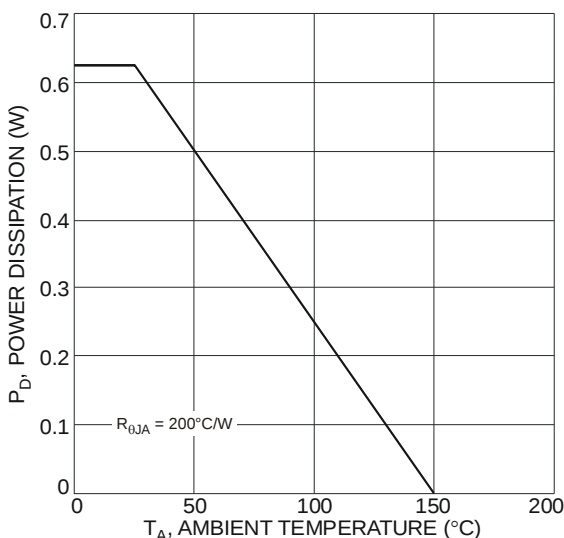


Fig. 1 Power Dissipation vs. Ambient Temperature

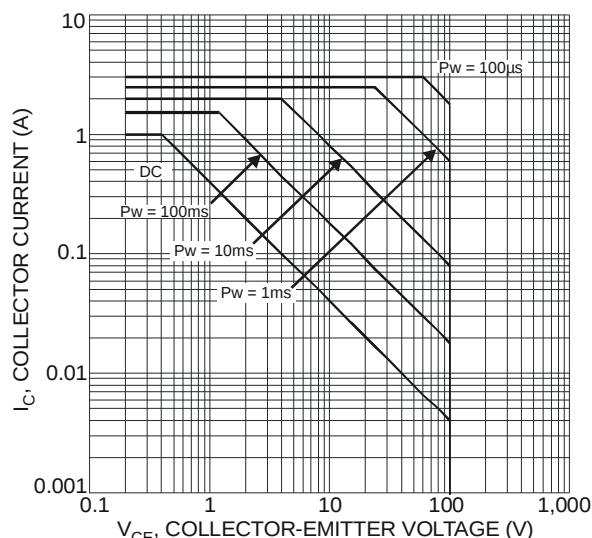


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

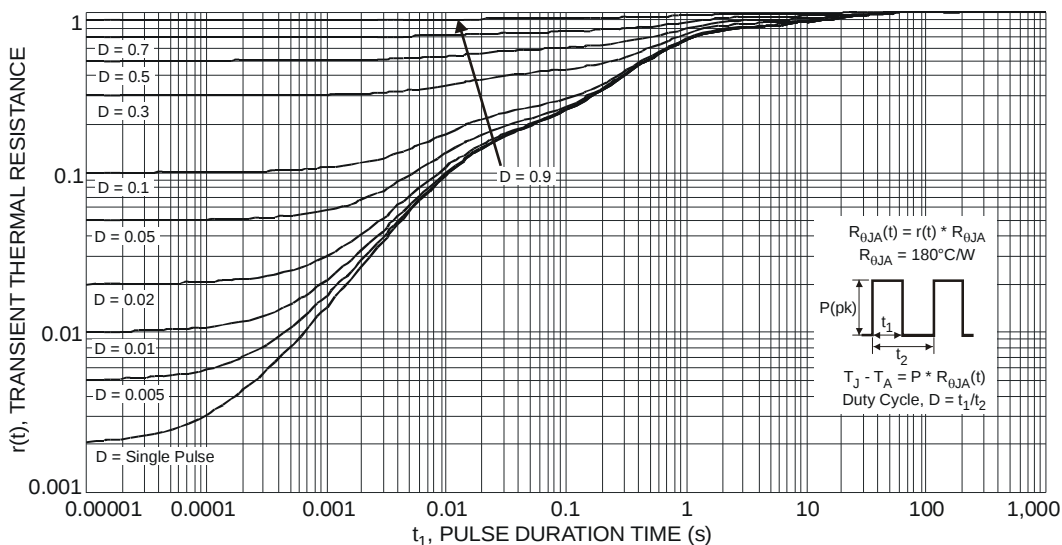


Fig. 3 Transient Thermal Response

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Collector-Base Breakdown Voltage	BV_{CBO}	120	—	—	V	$I_C = 100\mu\text{A}$, $I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	100	—	—	V	$I_C = 10\text{mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	$I_E = 100\mu\text{A}$, $I_C = 0$
Collector Cutoff Current	I_{CBO}	—	—	100	nA	$V_{CB} = 80\text{V}$, $I_E = 0$
Collector Cutoff Current	I_{CES}	—	—	50	μA	$V_{CB} = 80\text{V}$, $I_E = 0$, $T_A = 150^\circ\text{C}$
Collector Cutoff Current	I_{CES}	—	—	100	nA	$V_{CE} = 80\text{V}$, $V_{BE} = 0$
Emitter Cutoff Current	I_{EBO}	—	—	100	nA	$V_{EB} = 4\text{V}$, $I_C = 0$
ON CHARACTERISTICS (Note 5)						
DC Current Gain	h_{FE}	150 150 100 80	— — — —	— 500 — —	V	$V_{CE} = 10\text{V}$, $I_C = 1\text{mA}$ $V_{CE} = 10\text{V}$, $I_C = 250\text{mA}$ $V_{CE} = 10\text{V}$, $I_C = 500\text{mA}$ $V_{CE} = 10\text{V}$, $I_C = 1\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	— — —	— — —	40 120 200	mV	$I_C = 100\text{mA}$, $I_B = 10\text{mA}$ $I_C = 500\text{mA}$, $I_B = 50\text{mA}$ $I_C = 1\text{A}$, $I_B = 100\text{mA}$
Collector-Emitter Saturation Resistance	$R_{CE(sat)}$	—	—	200	m Ω	$I_C = 1\text{A}$, $I_B = 100\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	—	1.05	V	$I_C = 1\text{A}$, $I_B = 100\text{mA}$
Base-Emitter Turn On Voltage	$V_{BE(on)}$	—	—	0.9	V	$V_{CE} = 10\text{V}$, $I_C = 1\text{A}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{obo}	—	—	7.5	pF	$V_{CB} = 10\text{V}$, $f = 1.0\text{MHz}$
Current Gain-Bandwidth Product	f_T	100	—	—	MHz	$V_{CE} = 10\text{V}$, $I_C = 50\text{mA}$, $f = 100\text{MHz}$

Notes: 5. Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle $\leq 2\%$.

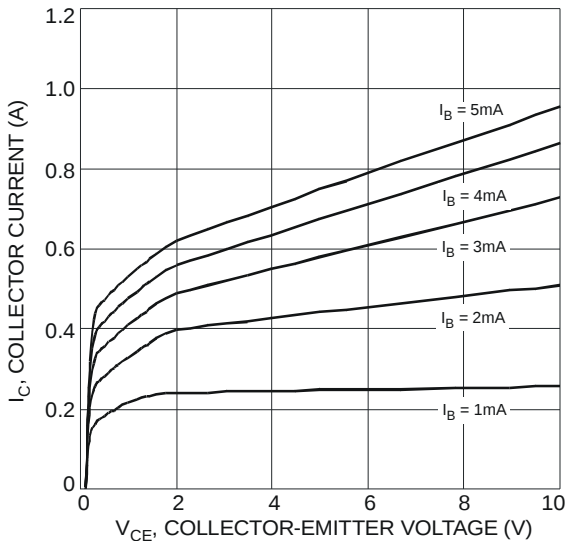


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

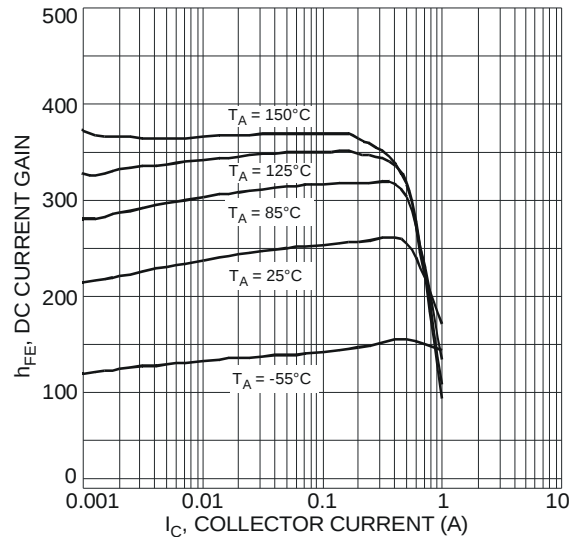


Fig. 5 Typical DC Current Gain vs. Collector Current

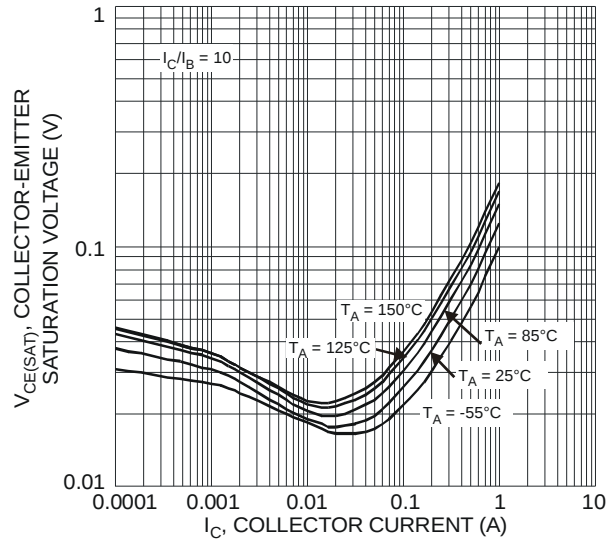


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

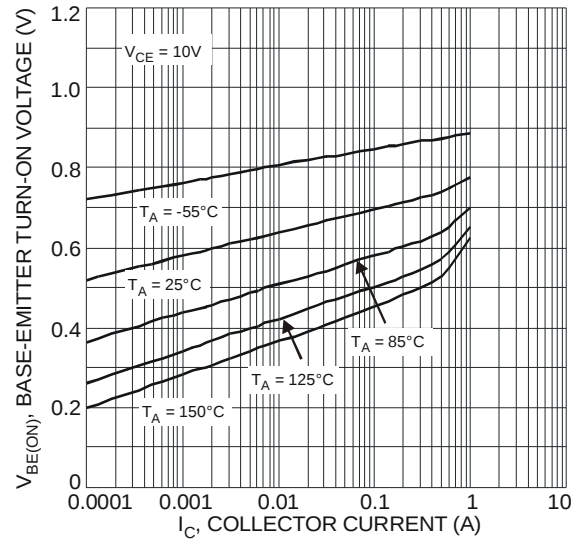


Fig. 7 Typical Base-Emitter Turn-On Voltage vs. Collector Current

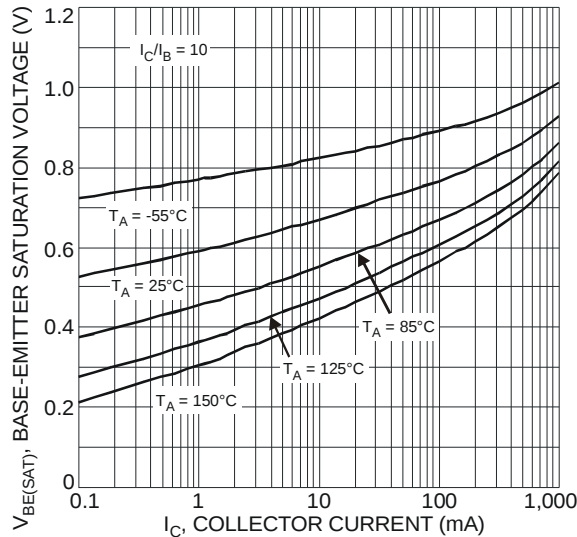
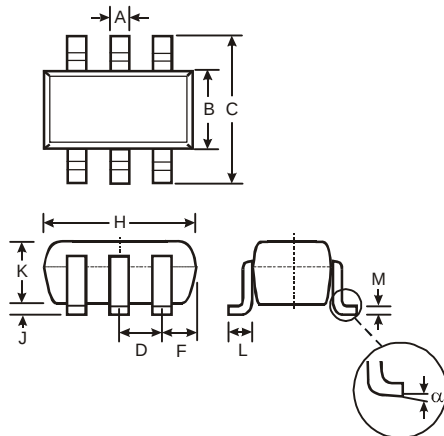


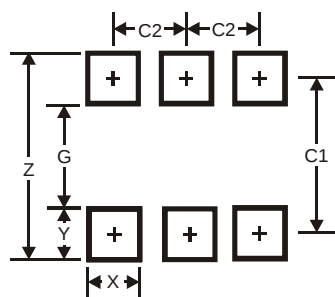
Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current

Package Outline Dimensions



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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